



(12) **Patent Application Publication**
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(43) **Pub. Date:** **Jun. 27, 2024**

Publication Classification

(51) **Int. Cl.**
H01L 27/118 (2006.01)
H01L 29/423 (2006.01)

(52) **U.S. Cl.**
CPC .. *H01L 27/11807* (2013.01); *H01L 29/42392*
(2013.01); *H01L 2027/11829* (2013.01)

(57) **ABSTRACT**

Semiconductor devices and methods of forming the same are provided. Semiconductor devices may include first and second active patterns on a substrate. Each of the first and second active patterns may extend in a first direction. The first and second active patterns may be aligned along the first direction and may be separated by a first trench extending in a second direction. The first trench may define a first sidewall of the first active pattern. The semiconductor devices may also include a channel pattern including first and second semiconductor patterns stacked on the first active pattern, a dummy gate electrode on the channel pattern and extending in the second direction, and a gate spacer on one side of the dummy gate electrode, the one side of the dummy gate electrode being adjacent to the first trench. The gate spacer may cover a first sidewall of the first active pattern.

Related U.S. Application Data

(60) Division of application No. 17/199,497, filed on Mar. 12, 2021, now Pat. No. 11,978,739, which is a continuation of application No. 16/295,198, filed on Mar. 7, 2019, now Pat. No. 10,978,486.

(30) **Foreign Application Priority Data**

Jul. 27, 2018 (KR) 10-2018-0087911

